

### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Drain Current (Note 5)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-10 -8	А
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-90	Α

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	2.5	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	50	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

Notes: 5. Device mounted on 2 oz. Copper pads on FR-4 PCB.

6. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .

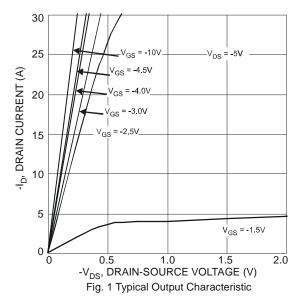
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.6	-0.77	-1.1	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
	R <sub>DS(ON)</sub>		8	13	mΩ	$V_{GS} = -10V, I_{D} = -10A$	
Static Drain-Source On-Resistance			11	16		$V_{GS} = -4.5V, I_{D} = -9A$	
			17	22		$V_{GS} = -2.5V, I_{D} = -8A$	
Forward Transconductance	g <sub>fs</sub>	_	28	_	S	$V_{DS} = -10V, I_{D} = -10A$	
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-0.5	-0.68	-1.2	V	$V_{GS} = 0V, I_{S} = -3A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		2444	_	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz	
Output Capacitance	Coss		594	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		556	_	pF		
Gate Resistance	R <sub>G</sub>		2.0	_	Ω	$V_{GS} = 0V$ , $V_{DS} = 0V$ , $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 8)							
Total Gate Charge	$Q_g$		28.1 56.9	_		$V_{DS} = -10V$ , $V_{GS} = -4.5V$ , $I_{D} = -10A$ $V_{DS} = -10V$ , $V_{GS} = -10V$ , $I_{D} = -10A$	
Gate-Source Charge	Q <sub>as</sub>		3.4	_	nC	$V_{DS} = -10V, V_{GS} = -10V, I_{D} = -10A$	
Gate-Drain Charge	Q <sub>ad</sub>		11.9	_	1	$V_{DS} = -10V$ , $V_{GS} = -10V$ , $I_{D} = -10A$	
Turn-On Delay Time	t <sub>D(ON)</sub>		7.5	15			
Turn-On Rise Time	t <sub>R</sub>		9.9	20	1	$V_{DD} = -15V$ , $I_{D} = -1A$ , $V_{GS} = -10V$ ,	
Turn-Off Delay Time	t <sub>D(OFF)</sub>		108.0	216	ns	$R_{GEN} = 6\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	76.5	153	1		

Notes: 7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





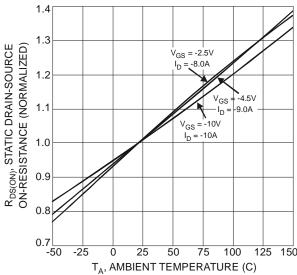


Fig. 3 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature

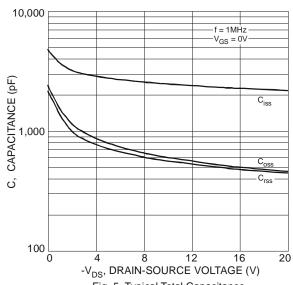
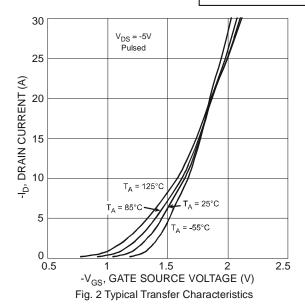


Fig. 5 Typical Total Capacitance



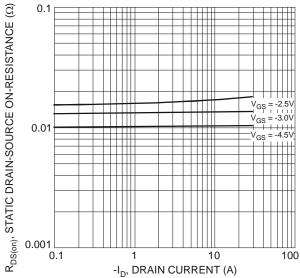


Fig. 4 On-Resistance vs. Drain Current and Gate Voltage

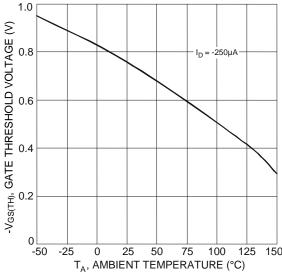
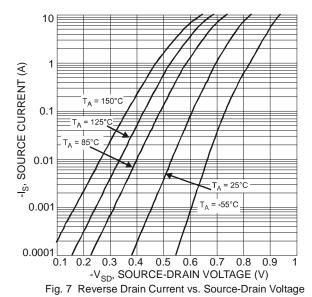
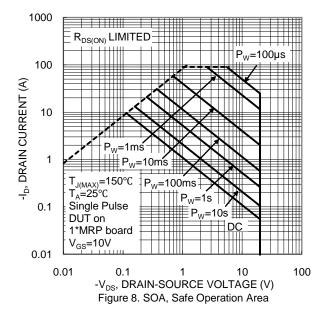


Fig. 6 Gate Threshold Variation vs. Ambient Temperature



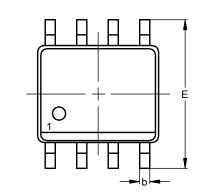


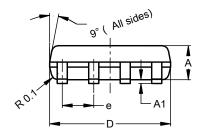


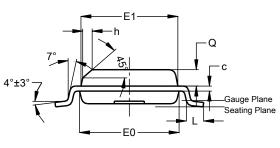


## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





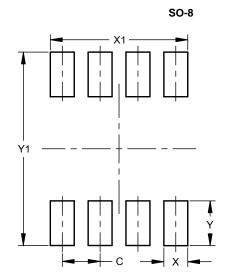


SO-8

SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
Y1	6.50



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